

KBP200G – KBP2010G

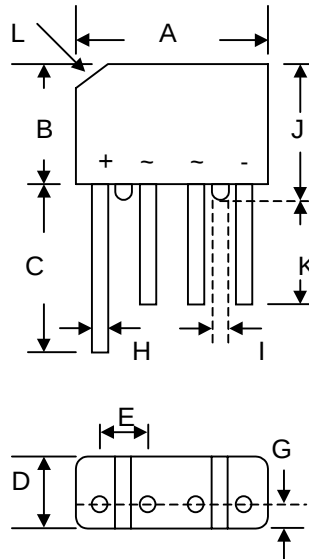
2.0A GLASS PASSIVATED BRIDGE RECTIFIER

Features

- Glass Passivated Die Construction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- Ideal for Printed Circuit Boards

Mechanical Data

- Case: Molded Plastic
- Terminals: Plated Leads Solderable per MIL-STD-202, Method 208
- Polarity: As Marked on Body
- Weight: 1.7 grams (approx.)
- Mounting Position: Any
- Marking: Type Number



KBP		
Dim	Min	Max
A	14.22	15.24
B	10.67	11.68
C	15.2	—
D	4.57	5.08
E	3.60	4.10
G	2.16	2.67
H	0.76	0.86
I	1.52	—
J	11.68	12.7
K	12.7	—
L	3.2 x 45° Typical	
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load.
 For capacitive load, derate current by 20%.

Characteristic	Symbol	KBP 200G	KBP 201G	KBP 202G	KBP 204G	KBP 206G	KBP 208G	KBP 2010G	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	50	100	200	400	600	800	1000	V
RMS Reverse Voltage	V _{R(RMS)}	35	70	140	280	420	560	700	V
Average Rectified Output Current (Note 1) @T _A = 50°C	I _O	2.0							A
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	60							A
Forward Voltage (per element) @I _F = 2.0A	V _{FM}	1.1							V
Peak Reverse Current @T _A = 25°C At Rated DC Blocking Voltage @T _A = 100°C	I _{RM}	10 500							μA
Rating for Fusing (t<8.3ms)	I ² t	15							A ² s
Typical Junction Capacitance per element (Note 2)	C _j	25							pF
Typical Thermal Resistance (Note 3)	R _{θJA}	30							K/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +165							°C

Note: 1. Leads maintained at ambient temperature at a distance of 9.5mm from the case.
 2. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.
 3. Thermal resistance junction to ambient mounted on PC board with 12mm² copper pad.

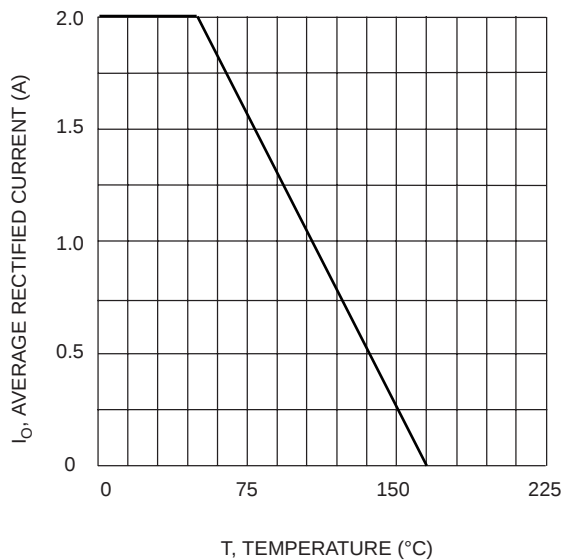


Fig. 1 Forward Current Derating Curve

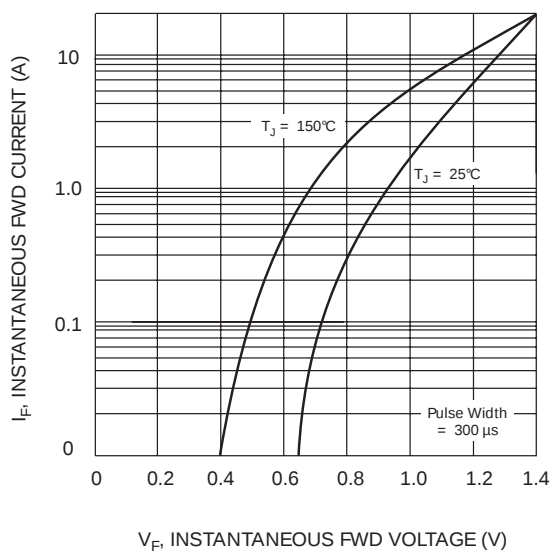


Fig. 2 Typical Fwd Characteristics

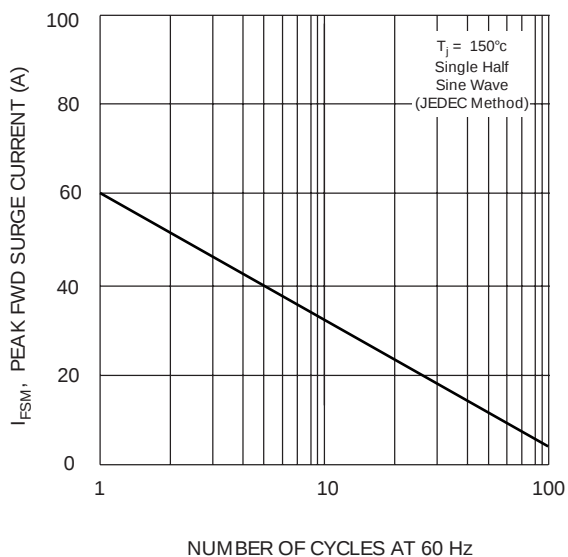


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current

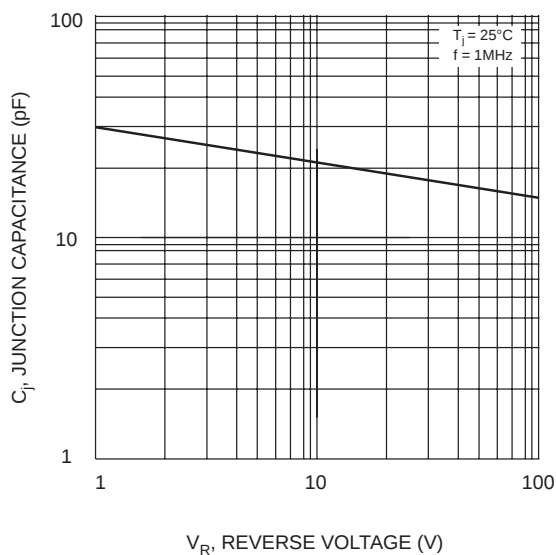


Fig. 4 Typical Junction Capacitance

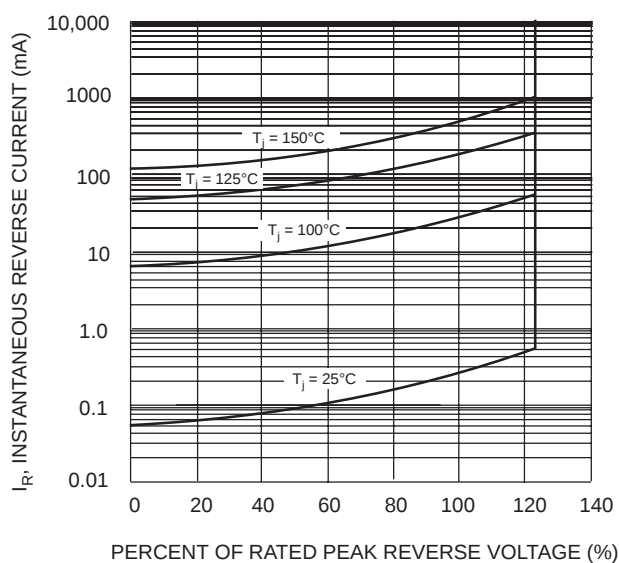


Fig. 5 Typical Reverse Characteristics

ORDERING INFORMATION

Product No.	Package Type	Shipping Quantity
KBP200G	SIL Bridge	1000 Units/Box
KBP201G	SIL Bridge	1000 Units/Box
KBP202G	SIL Bridge	1000 Units/Box
KBP204G	SIL Bridge	1000 Units/Box
KBP206G	SIL Bridge	1000 Units/Box
KBP208G	SIL Bridge	1000 Units/Box
KBP2010G	SIL Bridge	1000 Units/Box

Shipping quantity given is for minimum packing quantity only. For minimum order quantity, please consult the Sales Department.

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WARNING: DO NOT USE IN LIFE SUPPORT EQUIPMENT. WTE power semiconductor products are not authorized for use as critical components in life support devices or systems without the express written approval.

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